

WHAT IS CLAIMED IS:

- 1            1. A semiconductor device comprising:  
2        *545 B1>* a. a leadframe including a plurality of leads extending therefrom, a first  
3        source attach area on a first surface of the leadframe and a first gate attach area, and a second  
4        source attach area on a second surface of the leadframe and a second gate attach area;  
5            b. at least two dies, a first of which is coupled to the first source and gate  
6        attach areas and a second of which is coupled to the second source and gate attach areas;  
7            c. a drain connection assembly coupled to a drain region of the first die;  
8        and,  
9            a body, the body being coupled to the semiconductor device such that a drain  
10      region of the second die is exposed.
- 1            2. A semiconductor device in accordance with claim 1 wherein at least  
2        one of the dies is a bumped die.
- 1            3. A semiconductor device in accordance with claim 2 wherein both dies  
2        are bumped dies.        *B*
- 1            4. A semiconductor device in accordance with claim 1 wherein the drain  
2        connection assembly comprises a drain clip and a lead rail adjacent an edge of the drain clip.

- 1            5. A method of making a semiconductor device, the method  
2        comprising:  
3            providing a leadframe including a plurality of leads extending therefrom, a  
4        first source attach area on a first surface of the leadframe and a first gate attach area, and a  
5        second source attach area on a second surface of the leadframe and a second gate attach area;  
6            bonding a first die to the first source and gate attach areas with solder;  
7            reflowing the solder;  
8            bonding a second die to the second source and gate attach areas with second  
9        solder;  
10          bonding a drain connection assembly to a drain region of the second die with  
11        third solder;  
12          reflowing at least the third solder; and  
13          coupling a body to the semiconductor device such that a drain region of the  
14        second die is exposed.

1                   6. A method in accordance with claim 5 further comprising reflowing the  
2 second solder prior to bonding the drain connection assembly to the drain region of the  
3 second die.

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